

Contents

Preface	v
Acknowledgements	xi
1. Fundamentals	1
1.1 Introduction.....	1
1.2 Blackbody radiation and flux transfer	4
1.2.1 Blackbody radiation.....	4
1.2.2 Flux transfer	8
1.3 Signal and noise in photodetection.....	13
1.3.1 Optical signal of a photoconductor.....	14
1.3.2 Noise in a photoconductor	19
2. Energy Levels in One-Dimensional Quantum Wells	26
2.1 Analytical method.....	27
2.2 Wentzel-Kramers-Brillouin approximation.....	30
2.3 Kronig-Penney model.....	35
2.4 Transfer-matrix method	54
3. Quantum Wells in Crystal Lattices	73
3.1 Finite in-plane momentum.....	73
3.2 Crystal symmetries and band structure of GaAs	77
3.2.1 Basic properties of a group.....	77
3.2.2 Symmetry group of GaAs crystal lattice.....	81
3.3 k-p perturbation theory.....	86
3.4 Band nonparabolicity.....	93
4. Quantum Wells in the Presence of Interaction	99
4.1 Direct Coulomb interaction	99
4.2 Electron-electron interaction	102
4.3 Electron-phonon interaction	110
4.4 Static electric field.....	114
4.5 Oscillating electric field.....	117
5. Intersubband Transition in Quantum wells	122
5.1 Theory of dipole transition	122
5.2 Intersubband transition in superlattices	125
5.3 Bound-to-bound intersubband transition.....	129
5.4 Bound-to-continuum transition.....	130
5.5 Bound-to-quasi-bound transition.....	143
5.6 Bound-to-miniband transition.....	144

VIII Contents

5.7 Absorption lineshape.....	146
5.7.1 Bound-to-continuum transition in thick barrier quantum wells.....	147
5.7.2 Bound-to-miniband transition in thin barrier quantum wells	152
5.7.3 Bound-to-bound transition in thick barrier quantum wells.....	155
5.8 Absorption strength.....	156
6. Optical Coupling for Quantum Well Infrared Photodetectors.....	159
6.1 Edge coupling	159
6.2 Grating coupling.....	163
6.2.1 Grating design	163
6.2.2 Grating efficiency.....	171
6.2.3 Grating coupled lineshape.....	178
6.3 Random scattering reflector	182
6.4 Corrugated Quantum Well Infrared Photodetectors.....	189
7. Hot-Electron Transistors.....	201
7.1 Hot-electron injection in HET	202
7.2 Hot-electron energy relaxation.....	207
7.2.1 Electron-phonon interaction.....	208
7.2.2 Electron-electron interaction.....	215
7.2.3 Combined phonon and plasmon scattering.....	216
7.3 Experimental result from a HET.....	222
7.4 Magnetophonon effect	226
7.5 Band nonparabolicity measured by hot-electron injection	229
7.6 Global quantization.....	233
8. Excitation Hot-Electron Spectroscopy of Quantum Wells.....	238
8.1 Thermally stimulated hot-electron spectroscopy.....	238
8.1.1 Direct transport process	241
8.1.2 Thermally assisted tunneling.....	245
8.1.3 Thermally assisted impurity tunneling.....	249
8.2 Optically stimulated hot-electron spectroscopy.....	251
8.3 Electron trajectory in MQW	254
9. Transport Properties of Multiple Quantum Well Structures.....	258
9.1 Sequential resonant tunneling	258
9.2 Thermally assisted tunneling.....	265
9.3 Thermionic miniband transport.....	268
9.4 Thermal activation in multiple quantum well structures	273

10. Quantum Well Infrared Photodetector	279
10.1 Photoconductivity of MQW	279
10.2 Capture probability	281
10.3 Photoelectron lifetime	286
10.4 Effects of photoelectron mobility	288
10.5 Responsivity of thin barrier MQW	291
10.6 Noise characteristics of QWIP	294
10.7 Optimization of QWIP	299
10.7.1 Detector barrier height	300
10.7.2 Cutoff wavelength	301
10.7.3 Doping density	302
10.7.4 Bias polarity	304
10.7.5 Barrier width	306
10.7.6 Barrier profile	307
10.7.7 Bound-to-miniband QWIP	308
10.7.8 Number of wells	312
10.7.9 Photovoltaic detectors	313
10.8 Avalanche multiplication in QWIPs	315
11. Infrared Hot-Electron Transistor	321
11.1 Figure of merit	321
11.2 Dark current requirement	322
11.3 Functions of an IHET	323
11.4 High detectivity IHET	325
11.4.1 IHET with a thin barrier QWIP	326
11.4.2 IHET with a thick barrier QWIP	332
11.5 IHET for small $NE\Delta T$	334
11.6 IHET for high temperature operation	342
11.6.1 IHET with $\lambda_c = 14 \mu\text{m}$	343
11.6.2 Energy relaxation of photoelectrons in the base	349
11.6.3 IHET with $\lambda_c = 10.8 \mu\text{m}$	351
11.7 Long wavelength IHET	352
11.8 Signal amplification of IHET	358
11.8.1 Equivalent circuit of an IHET	358
11.8.2 Experimental results	361
12. Noise Properties of Infrared Hot-Electron Transistor	366
12.1 Basic statistics of noise	366
12.2 Noise bandwidth	367
12.3 Classical noise from an IHET	369
12.4 Separation of g-r noise and partition noise	371
12.5 Quantum partition noise	374

X Contents

12.6 1/f noise of QWIP	380
13. Multi-Color QWIP and IHET	382
13.1 Two-stack MQW approach	383
13.2 Coupled quantum well for multi-color detection.....	385
13.3 Photoexcited coherent tunneling.....	389
13.4 Thick barrier QWIP for three-color detection.....	393
13.5 Multi-color IHET	394
14. Performance of Quantum Well Infrared Photodetectors.....	401
14.1 Background limited temperature	401
14.2 Corrugated-QWIP for T_{BLIP} improvement	406
14.3 Detectivity of QWIPs.....	410
14.4 A case study	411
14.5 Quantum well detector arrays	413
14.6 Final remarks.....	416
Subject Index	418